



## Surface mount diode

## Ultrafast silicon rectifier diodes

### EGL 1A ... EGL 1M

**Forward Current: 1 A**

**Reverse Voltage: 50 to 1000 V**

### Features

- Max. solder temperature: 260°C
- Plastic material has UL classification 94V-0
- green ring denotes " cathode " and " ultrafast switching device "
- colored ring denotes " repetitive peak reverse voltage "

### Mechanical Data

- Plastic case MiniMelf / SOD-80 / DO-213AA
- Weight approx.: 0,04 g
- Terminals: plated terminals solderable per MIL-STD-750
- Mounting position: any
- Standard packaging: 2500 pieces per reel

- 1) Max. temperature of the terminals  $T_T = 75$  °C
- 2)  $I_F = 1$  A,  $T_j = 25$  °C
- 3)  $T_A = 25$  °C
- 4) Mounted on P.C. board with 25 mm<sup>2</sup> copper pads at each terminal

Type	Polarity color band	Repetitive peak reverse voltage $V_{RRM}$ V	Surge peak reverse voltage $V_{RSM}$ V	Maximum forward voltage $T_j = 25$ °C $I_F = 1$ A $V_F^{(2)}$ V	Maximum reverse recovery time $I_F = 0,5$ A $I_R = 1$ A $I_{RR} = 0,25$ A $t_{rr}$ ns
EGL 1A	gray	50	50	1,25	50
EGL 1B	red	100	100	1,25	50
EGL 1D	orange	200	200	1,25	50
EGL 1G	yellow	400	400	1,35	50
EGL 1J	green	600	600	1,9	75
EGL 1K	blue	800	800	1,9	75
EGL 1M	violett	1000	1000	1,9	75

### Absolute Maximum Ratings $T_A = 25$ °C, unless otherwise specified

Symbol	Conditions	Values	Units
$I_{FAV}$	Max. averaged fwd. current, R-load, $T_T = 75$ °C <sup>1)</sup>	1	A
$I_{FRM}$	Repetitive peak forward current $f > 15$ Hz <sup>1)</sup>	8	A
$I_{FSM}$	Peak fwd. surge current 60 Hz half sinus-wave <sup>3)</sup>	25	A
$I^2t$	Rating for fusing, $t < 10$ ms <sup>3)</sup>	2	A <sup>2</sup> s
$R_{thA}$	Max. thermal resistance junction to ambient <sup>4)</sup>	150	K/W
$R_{thT}$	Max. thermal resistance junction to terminals	60	K/W
$T_j$	Operating junction temperature	- 50 ... + 175	°C
$T_s$	Storage temperature	- 50 ... + 175	°C

### Characteristics $T_A = 25$ °C, unless otherwise specified

Symbol	Conditions	Values	Units
$I_R$	Maximum leakage current, $T_j = 25$ °C; $V_R = V_{RRM}$ $T_j = 125$ °C; $V_R = V_{RRM}$	<5 <50	µA µA
$C_j$	Typical junction capacitance (at MHz and applied reverse voltage of V)	-	pF
$Q_{rr}$	Reverse recovery charge ( $U_R = V$ ; $I_F = A$ ; $dI_F/dt = A/ms$ )	-	µC
$E_{RSM}$	Non repetitive peak reverse avalanche energy ( $I_R = mA$ ; $T_j =$ °C; inductive load switched off)	-	mJ



